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## **FDS5690**

## 60V N-Channel PowerTrench® MOSFET

## **General Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

## **Applications**

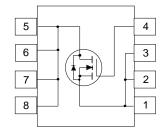
- DC/DC converter
- Motor drives

#### **Features**

• 7 A, 60 V. 
$$R_{DS(on)} = 0.028 \ \Omega \ @ \ V_{GS} = 10 \ V$$
  $R_{DS(on)} = 0.033 \ \Omega \ @ \ V_{GS} = 6 \ V.$ 

- Low gate charge (23nC typical).
- Fast switching speed.
- $\bullet$  High performance trench technology for extremely low  $R_{_{DS(ON)}}.$
- High power and current handling capability.





Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		60	V
V <sub>GSS</sub>	Gate-Source Voltage		<u>+</u> 20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	7	А
	- Pulsed		50	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range		-55 to +150	∘C

## **Thermal Characteristics**

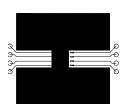
$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
R <sub>ÐJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS5690	FDS5690	13"	12mm	2500 units

Symbol	Parameter Test Conditions		Min	Тур	Max	Units
Off Char	acteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	60			V
ABV¤ss ∆TJ	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		57		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V			1	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
GSSR	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	2.5	4	V
ΔVGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$ , Referenced to 25°C		-5.9		mV/∘C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 6 \text{ V}, I_D = 6.5 \text{ A}$		0.022 0.037 0.025	0.028 0.050 0.033	Ω
D(on)	On-State Drain Current	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 5 V	25			Α
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 7 A		24		S
Dynamic	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V},$		1107		pF
Coss	Output Capacitance	f = 1.0 MHz		149		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			72		pF
Switchin	g Characteristics (Note 2)			1	ı	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, I_{D} = 1 \text{ A},$		10	18	ns
-r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		9	18	ns
d(off)	Turn-Off Delay Time			24	39	ns
f	Turn-Off Fall Time			10	18	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 30 \text{ V}, I_{D} = 7 \text{ A},$		23	32	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V,		4		nC
Q <sub>gd</sub>	Gate-Drain Charge	1		6.8		nC
	-	d Maximum Datings	1	I	ı	ı
<u>Drain-Sc</u> s	purce Diode Characteristics and Maximum Continuous Drain-Source Did				2.1	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2.1 \text{ A} \text{ (Note 2)}$		0.75	1.2	V

<sup>1.</sup> R<sub>eJA</sub> is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.





a) 50° C/W when mounted on a 0.5 in² pad of 2 oz. copper.

b) 105° C/W when mounted on a 0.02 in² pad of 2 oz. copper.

c) 125° C/W when mounted on a 0.003 in² pad of 2 oz. copper.



Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

## **Typical Characteristics**

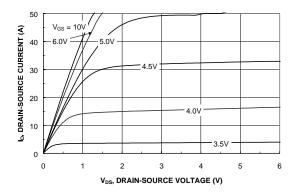


Figure 1. On-Region Characteristics.

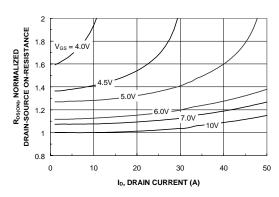


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

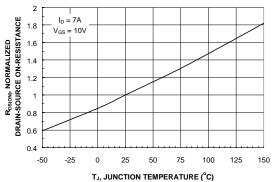


Figure 3. On-Resistance Variation with Temperature.

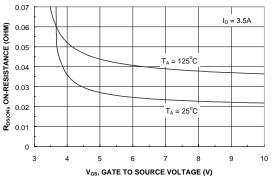


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

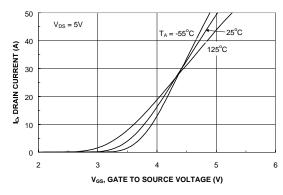


Figure 5. Transfer Characteristics.

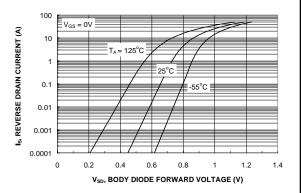
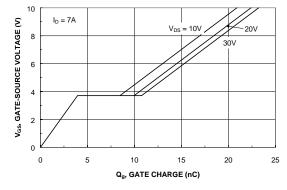


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics (continued)



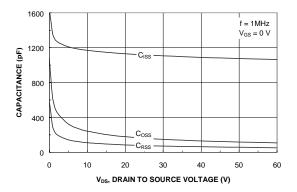
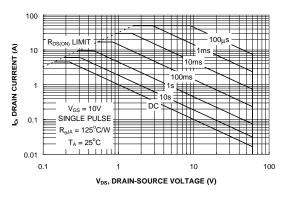


Figure 7. Gate Charge Characteristics.

Figure 8. Capacitance Characteristics.



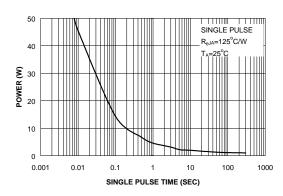


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

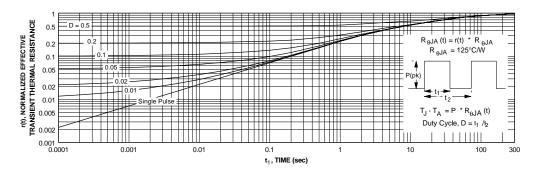


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.

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